In the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application:

1. (Currently Amended) A digital image sensor, comprising:

a first two-color photo-detector having a first photo-detector element ~~capable of~~ designed for absorbing blue light ~~within a first range of wavelengths~~ and a second photo-detector element ~~capable of~~ designed for absorbing complement of blue light ~~within a second range of wavelengths~~, said first photo-detector element being in an elevated relation with said second photo-detector element, said first photo-detector element being electrically isolated from said second photo-detector element; and

a second two-color photo-detector having a third photo-detector element ~~capable of~~ designed for absorbing complement of red light ~~within a third range of wavelengths~~ and a fourth photo-detector element ~~capable of~~ designed for absorbing red light ~~within a fourth range of wavelengths, said first, second, third and fourth range of wavelengths each being different from the other~~, said third photo-detector element being in an elevated relation with said fourth photo-detector element, said third photo-detector element being electrically isolated from said fourth photo-detector element.

2. (Original) The sensor of Claim 1, further comprising:

a substrate, said second photo-detector element being formed within said substrate.

3. (Original) The sensor of Claim 2, further comprising:

a dielectric layer between said first photo-detector element and said second photo-detector element, said dielectric layer electrically isolating said first photo-detector element from said second photo-detector element.

4. (Currently Amended) The sensor of Claim 1, wherein said first photo-detector element is formed of amorphous silicon having a thickness selected to absorb said blue light ~~within said first range of wavelengths~~ and pass said complement of blue light ~~within said second range of wavelengths, said second photo-detector detecting light within said second range of wavelengths passed by said first photo-detector element~~.

5. (Original) The sensor of Claim 1, wherein said first and second photo-detector elements are photodiodes.

6. (Original) The sensor of Claim 5, wherein said photodiodes are PIN photodiodes.

7. (Currently Amended) The sensor of Claim 1, further comprising:

a color filter in an elevated relation with said first photo-detector element, said color filter absorbing light within ~~another~~ a portion of said complement of blue light ~~range of wavelengths~~ and passing the rest of said complement of blue light ~~within said first and second ranges of wavelengths~~.

8. (Original) The sensor of Claim 7, further comprising:

a transparent metal conductor layer between said color filter and said first photo-detector element.

9. (Original) The sensor of Claim 1, further comprising:

circuitry for driving said first photo-detector element and said second photo-detector element, said first photo-detector element being in an elevated relation with said circuitry.

10-12. (Canceled)

13. (Currently Amended) The sensor of Claim 12, wherein said first photo-detector element produces a first color value, said second photo-detector element produces a second color value, said third photo-detector element produces a third color value and said fourth photo-detector element produces a fourth color value, and further comprising:

a third two-color photo-detector having a fifth photo-detector element in an elevated relation with a sixth photo-detector element, said fifth photo-detector element being electrically isolated from said sixth photo-detector element, said fifth photo-detector element ~~being capable of~~ designed for absorbing said blue light ~~within said first range of wavelengths~~ and producing a fifth color value, said sixth photo-detector element ~~being capable of~~ designed for absorbing said complement of blue light ~~within said second range of wavelengths~~ and producing a sixth color value; and

a fourth two-color photo-detector having a seventh photo-detector element in an elevated relation with an eighth photo-detector element, said seventh photo-detector element being electrically isolated from said eighth photo-detector element, said seventh

photo-detector element ~~being capable of~~ designed for absorbing said complement of red light ~~within said first range of wavelengths~~ and producing a seventh color value, said eighth photo-detector element ~~being capable of~~ designed for absorbing said red light ~~within said second range of wavelengths~~ and producing an eighth color value.

14. (Currently Amended) A digital image sensor, comprising:

a first two-color photo-detector having a first photo-detector element ~~capable of~~ designed for absorbing blue light ~~within a first range of wavelengths~~ and a second photo-detector element ~~capable of~~ designed for absorbing complement of blue light ~~within a second range of wavelengths~~, said first photo-detector element being in an elevated relation with said second photo-detector element;

a first dielectric layer between said first photo-detector element and said second photo-detector element;

a second two-color photo-detector having a third photo-detector element ~~capable of~~ designed for absorbing complement of red light ~~within a third range of wavelengths~~ and a fourth photo-detector element ~~capable of~~ designed for absorbing red light ~~within a fourth range of wavelengths, said first, second, third and fourth range of wavelengths each being different from the other~~, said third photo-detector element being in an elevated relation with said fourth photo-detector element; and

a second dielectric layer between said third photo-detector element and said fourth photo-detector element.

15. (Original) The sensor of Claim 14, further comprising:

a substrate, said second photo-detector element being formed within said substrate.

16. (Currently Amended) The sensor of Claim 14, wherein said first photo-detector element is formed of amorphous silicon having a thickness selected to absorb said blue light ~~within said first range of wavelengths~~ and pass said complement of blue light~~, said second photo-detector detecting light within said second range of wavelengths passed by said first photo-detector element~~.

17. (Currently Amended) The sensor of Claim 14, further comprising:

a color filter in an elevated relation with said first photo-detector element, , said color filter absorbing light within ~~another~~ a portion of said complement of blue light ~~range of wavelengths~~ and passing the rest of said complement of blue light ~~within said first and second ranges of wavelengths~~.

18. (Original) The sensor of Claim 17, further comprising:

a transparent metal conductor layer between said color filter and said first photo-detector element.

19. (Original) The sensor of Claim 14, further comprising:

circuitry for driving said first photo-detector element and said second photo-detector element, said first photo-detector element being in an elevated relation with said circuitry.

20-26. (Canceled).

27. (Currently Amended) The sensor of Claim 1, wherein said first photo-detector element is formed of amorphous silicon having a first thickness selected to absorb said blue light ~~within said first range of wavelengths~~ and said third photo-detector element is formed of amorphous silicon having a second thickness selected to absorb said complement of red light ~~within said third range of wavelengths~~.

28. (Currently Amended) The sensor of Claim 14, wherein said first photo-detector element is formed of amorphous silicon having a first thickness selected to absorb said blue light ~~within said first range of wavelengths~~ and said third photo-detector element is formed of amorphous silicon having a second thickness selected to absorb said complement of red light ~~within said third range of wavelengths~~.